

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MLN1027S** is Designed for Class A, Linear Applications up to 1.0 GHz.

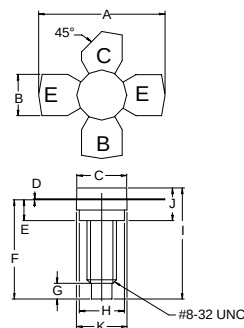
FEATURES:

- Class A Operation
- $P_G = 9.0$ dB at 0.5 W/1.0 GHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.250 A
V_{CBO}	40 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	25°C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10619

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	40			V
BV_{CEO}	$I_C = 1.0$ mA	28			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 24$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			3.5	pF
P_G	$V_{CE} = 20$ V $I_{CQ} = 100$ mA $f = 1.0$ GHz $P_{OUT} = 0.5$ W	9.0			dB